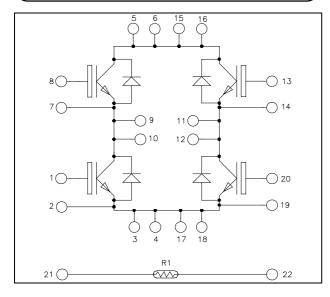


## Full - Bridge Trench + Field Stop IGBT3 Power Module



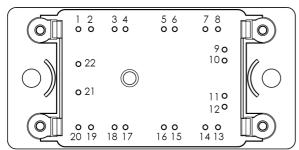


#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration



Pins 5/6/15/16; 3/4/17/18; 9/10; 11/12 must be shorted together

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

## All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

### Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
ī	Continuous Collector Current	$T_C = 25^{\circ}C$	100	
$I_{C}$	T <sub>C</sub>		75	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	140	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	250	W
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150$ °C	150A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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**Electrical Characteristics** (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $T_{j} = 25^{\circ}C$ $T_{c} = 75A$ $T_{j} = 150^{\circ}C$			1.5	1.9	V
V CE(sat)					1.7		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_{C} = 600 \mu A$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

**Dynamic Characteristics** (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			4620		
Coes	Output Capacitance	$V_{CE} = 25V$			300		pF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1MHz			140		
$Q_{G}$	Gate charge	V <sub>GE</sub> =±15V, I <sub>C</sub> =75A V <sub>CE</sub> =300V			0.8		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	hing (25°C)		110		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			45		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 75A$			200		
$T_{\mathrm{f}}$	Fall Time	$R_G = 4.7\Omega$			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_{C} = 75A$ $R_{G} = 4.7\Omega$			120		
$T_{r}$	Rise Time				50		ns
$T_{d(off)}$	Turn-off Delay Time				250		
$T_{\mathrm{f}}$	Fall Time				60		ĺ
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		0.35		mJ
Lon	Turn on Switching Energy	$V_{\text{Bus}} = 300 \text{V}$	$T_{j} = 150^{\circ}C$		0.6		1113
$E_{off}$	Turn-off Switching Energy	$I_C = 75A$	$T_j = 25^{\circ}C$		2.2		mJ
1011	Tain on Switching Divisy	$R_G = 4.7\Omega$	$T_{j} = 150^{\circ}C$		2.6		1110
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V ; V_{But}$ $t_p \le 6\mu s ; T_i = 15$			380		A
$R_{thJC}$	Junction to Case Thermal Resistance					0.60	°C/W



## Reverse diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage						V
$I_{RM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =600V				250	μΑ
$I_F$	DC Forward current		Tc = 80°C		75		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 75A$ $V_{GE} = 0V$	$T_{i} = 25^{\circ}C$ $T_{i} = 150^{\circ}C$		1.6	2	V
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 25$ °C		100		ns
-11		$I_{-} = 75 \Lambda$	$T_{j} = 150^{\circ}C$		150		
$Q_{rr}$	Reverse Recovery Charge	$\begin{split} I_F &= 75A \\ V_R &= 300V \\ di/dt &= 2000A/\mu s \end{split} .$	$T_j = 25$ °C		3.6		μС
Qrr	Q <sub>II</sub> recorded recovery charge		$T_j = 150$ °C		7.6		μΟ
$E_{r}$	Reverse Recovery Energy		$T_i = 25^{\circ}C$		0.85		mJ
Ŀr	Reverse Recovery Ellergy		$T_j = 150$ °C		1.8		1113
$R_{thJC}$	Junction to Case Thermal Resistance					0.98	°C/W

## **Temperature sensor NTC**

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		22		kΩ
$\Delta R_{25}/R_{25}$	Resistance tolerance			5	%
$\Delta B/B$	Beta tolerance			3	70
B <sub>25/100</sub>	$T_{25} = 298.16 \text{ K}$		3980		K

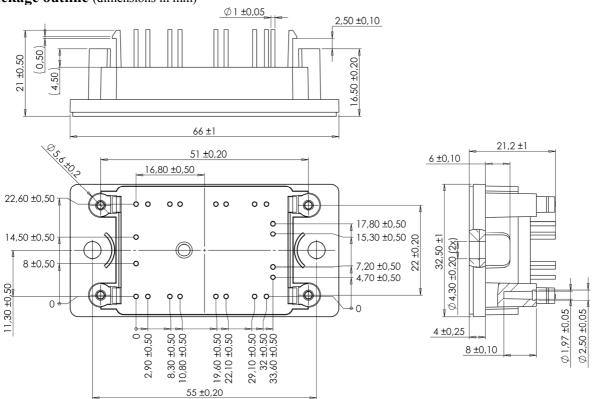
$$R_T = \frac{R_{25}}{\exp \left[ B_{25/100} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

## Thermal and package characteristics

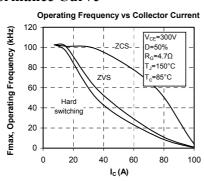
Symbol	Characteristic			Min	Тур	Max	Unit
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range			-40		175	
$T_{STG}$	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

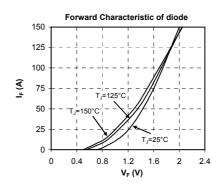


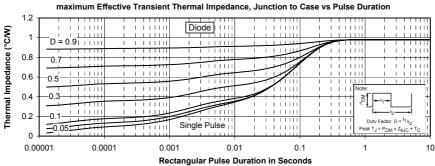
### Package outline (dimensions in mm)



## **Typical Performance Curve**

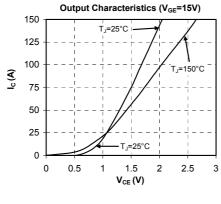


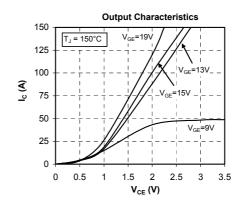


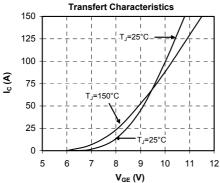


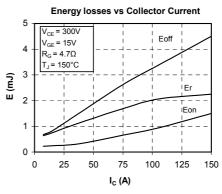
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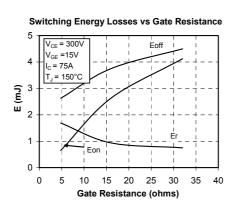


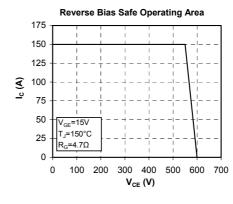


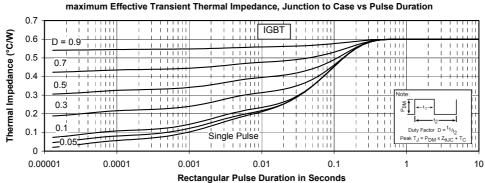














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